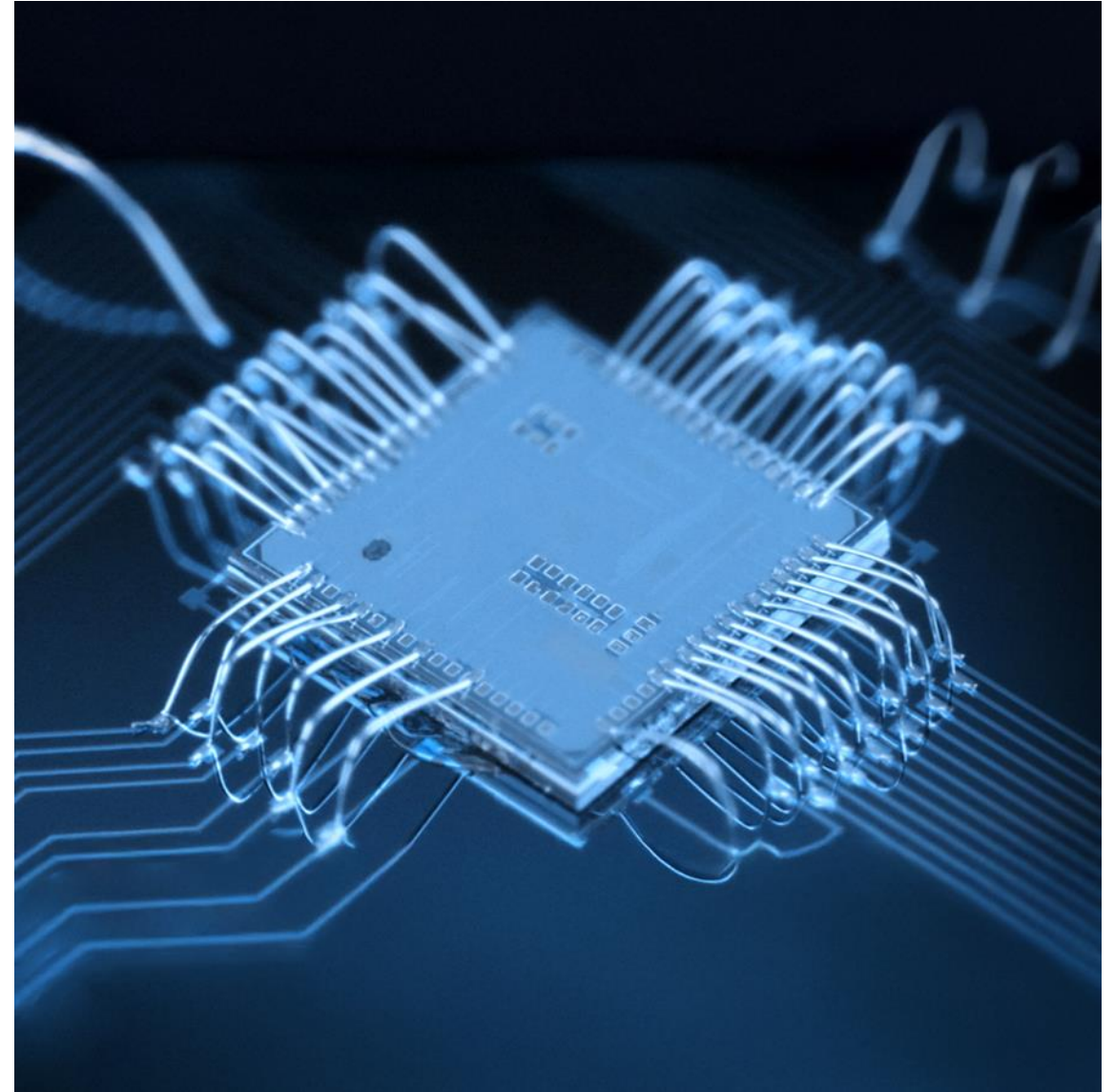


CRYOGENIC CMOS DESIGN FOR SCALABLE QUBIT CONTROL AND READOUT

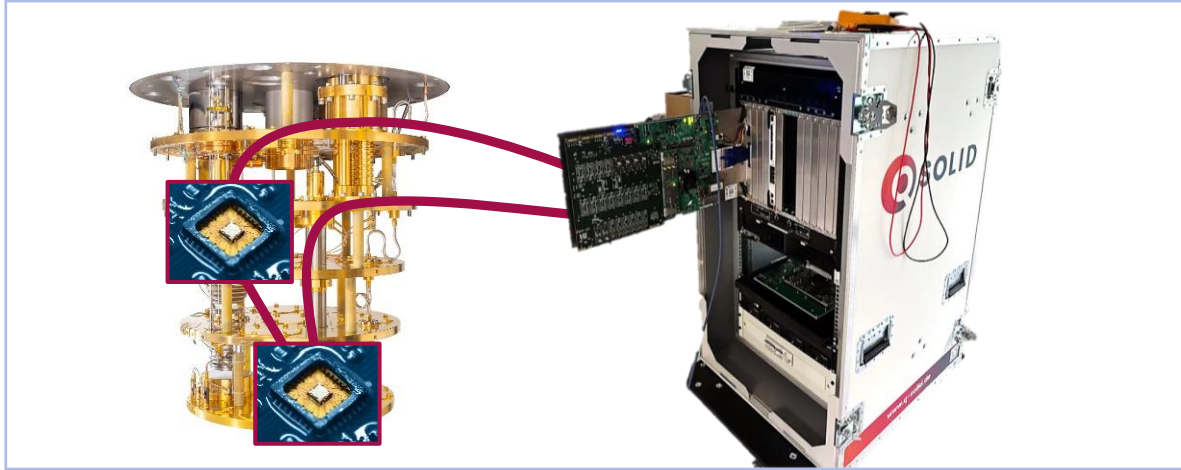
2026-05-21 | DENNIS NIELINGER, Jonas Bühler, Phanish Chava, Carsten Degenhardt, Andre Kruth, Sabitha Kusuma, Daniel Liebau, Jonas Mair, Lea Schreckenber, Patrick Vliex, Stefan van Waasen

CONTENT

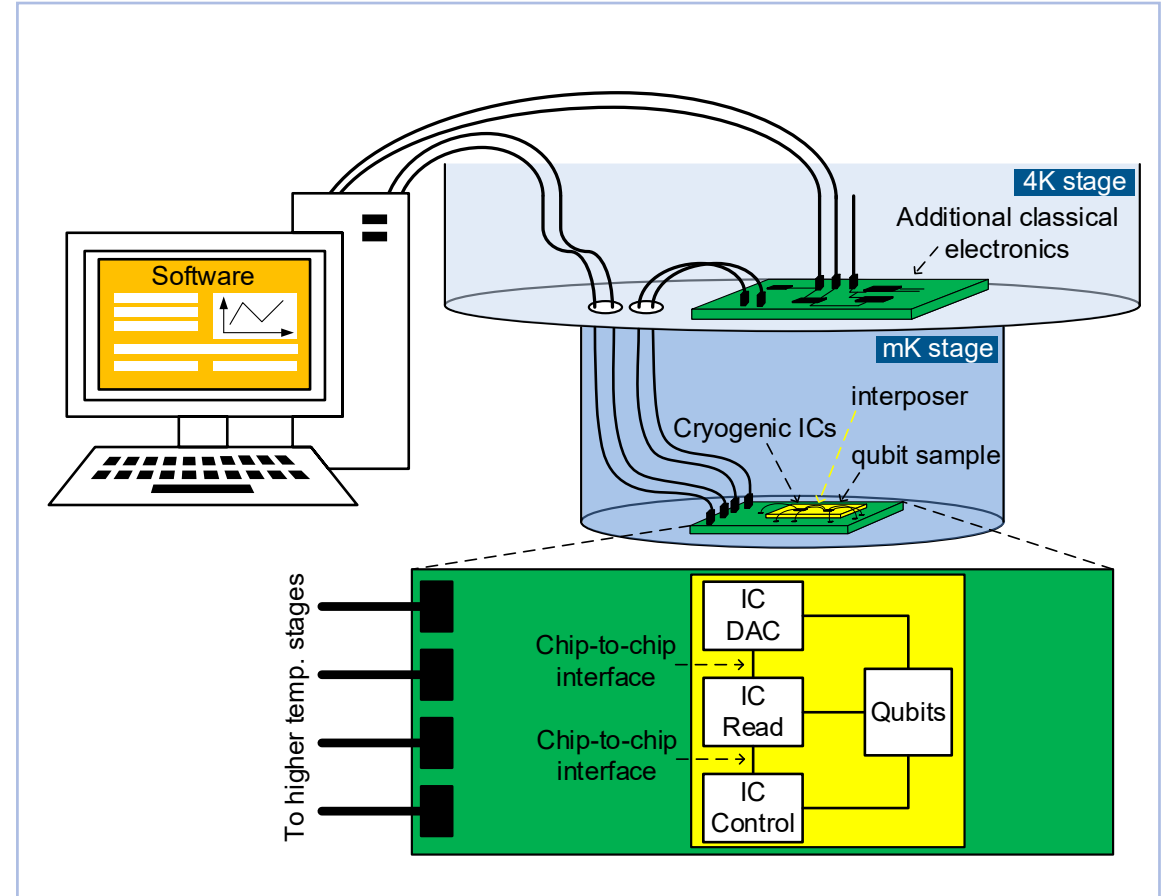
- **Designs in 65nm bulk and 22 nm FD-SOI**
 - Cryogenic measurement results
 - Lessons learned (what to watch out for)
- **Co-integration experiment with qubits at mK**
 - Thermal management
- **Other activities at ICA for QC:**
 - Cryogenic device measurement and modelling
 - Cryogenic photonic link (for superconducting qubits and cryo. electronics)



CRYOGENIC CMOS DESIGN



- Move (parts) of classical control & readout electronics closer to the qubit
- Consequence → operate at cryogenic temperature
- Cryogenic CMOS enables high-integration
 - Comply to ultra strict cooling power budget
- Qubits are evolving quickly → modular IC framework



DC BIAS

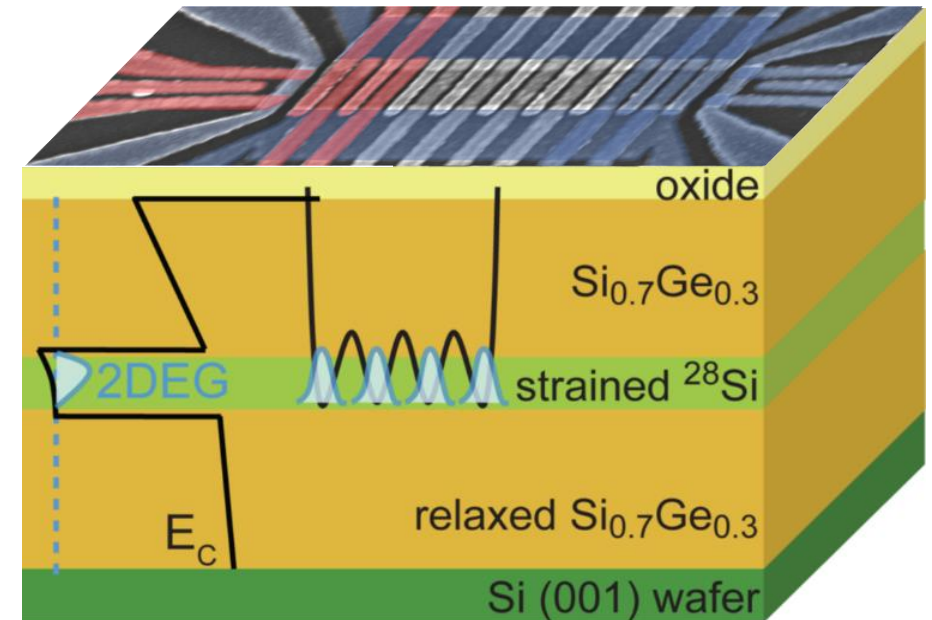
Specification

Specification for DC Bias via DAC

- Several uncorrelated bias voltage per qubit to form potential wells
- Voltage range up to approx. 1.7V
- A step size in the hundreds of μV

[3] I. Seidler, T. Struck, R. Xue et al., "Conveyor-mode single-electron shuttling in Si/SiGe for a scalable quantum computing architecture," npj Quantum Inf 8, 100, 2022.

Si/SiGe Architecture^[3]



DC BIAS

QUOCCA

Digital^[4]:

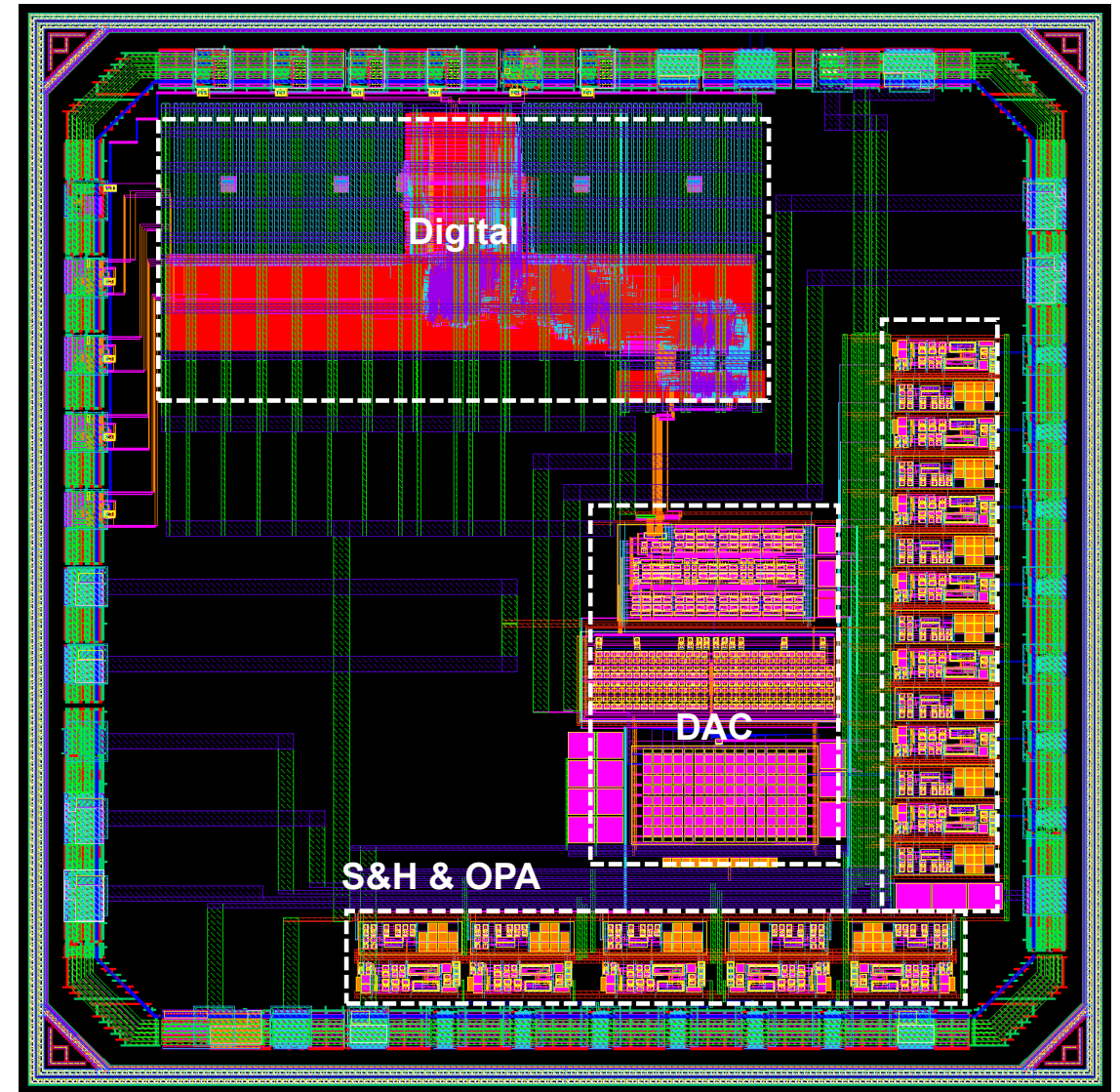
- JTAG Interface
- RISC-V Processor
- DAC FSM

Bias DAC:

- Charge-redistribution topology
 - Negligible static power

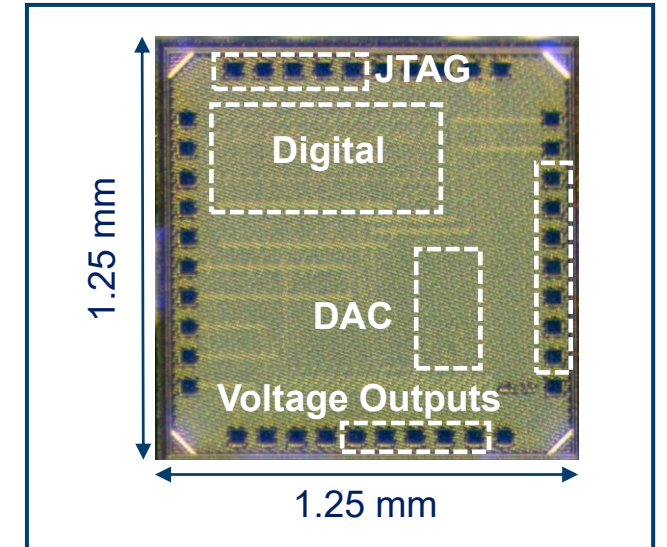
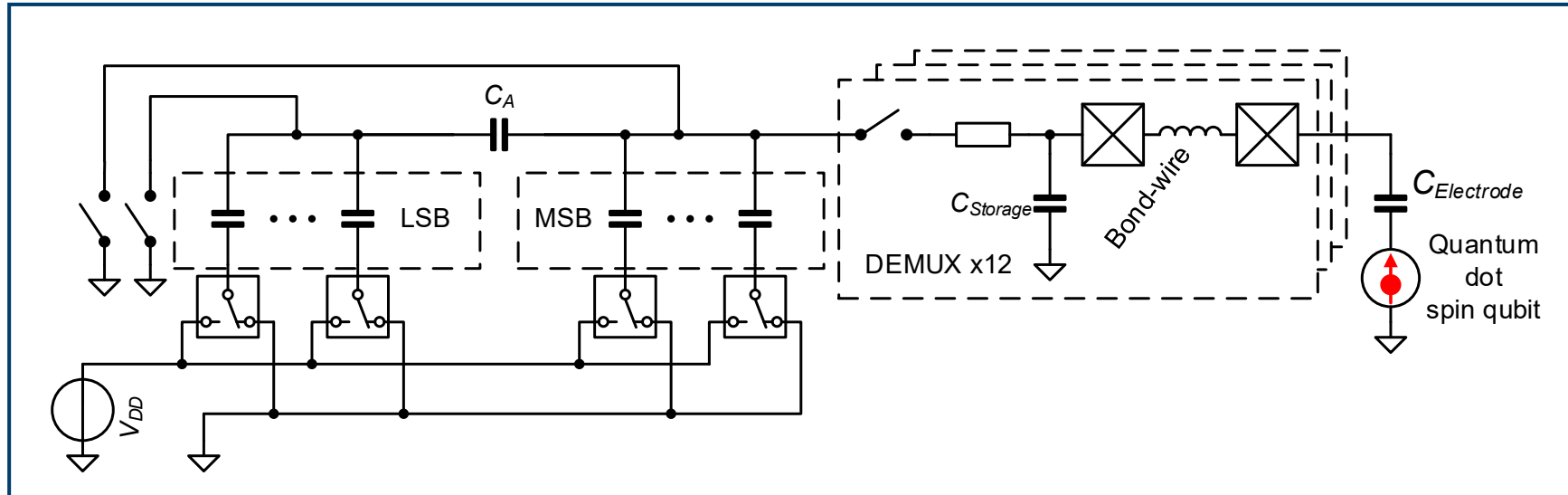
Sample & Hold Output Channel:

- Individual refreshable
- Testing amplifier



DC BIAS

CMOS Bias DAC

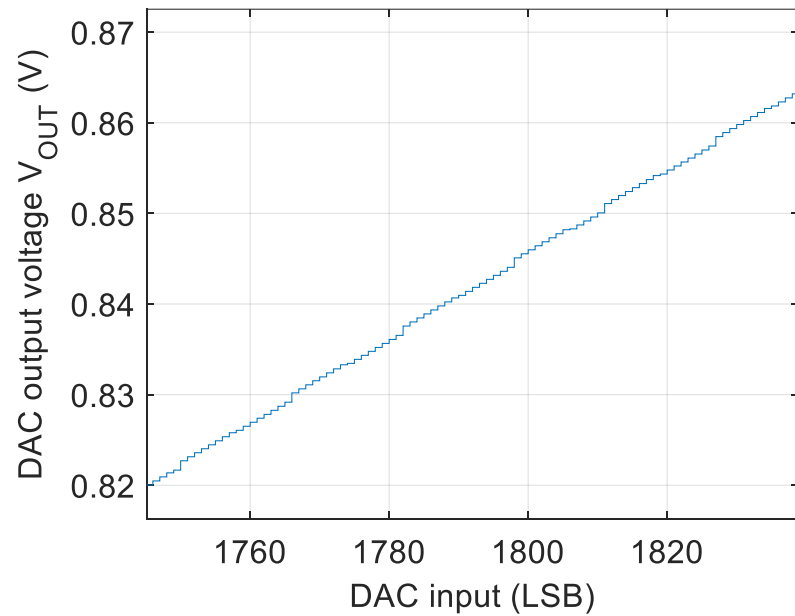


- No output buffer needed due to low leakage
 - Reduce power and noise
- Defined control of the DAC refresh
 - Internal or external trigger signal

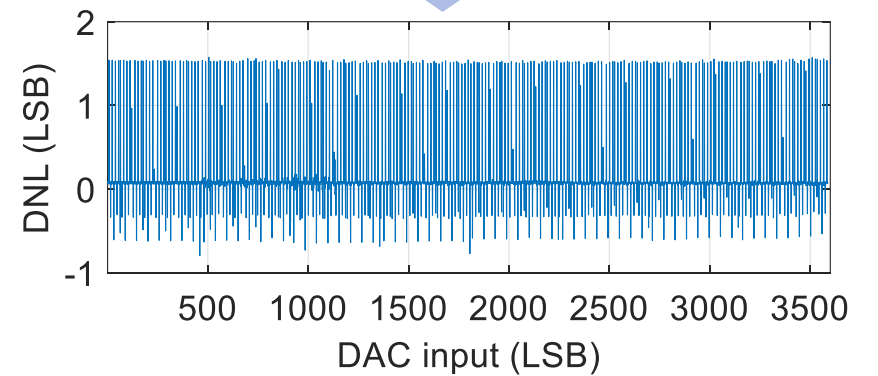
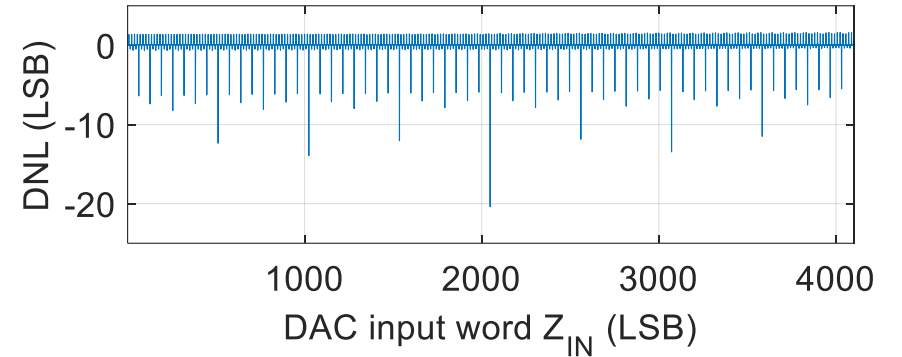
Characteristics	Specification
Output Channels	12
Voltage Range	0V to 1.8V
Resolution	12 Bit
Step Size	~ 439 μ V

DC BIAS

DAC Output



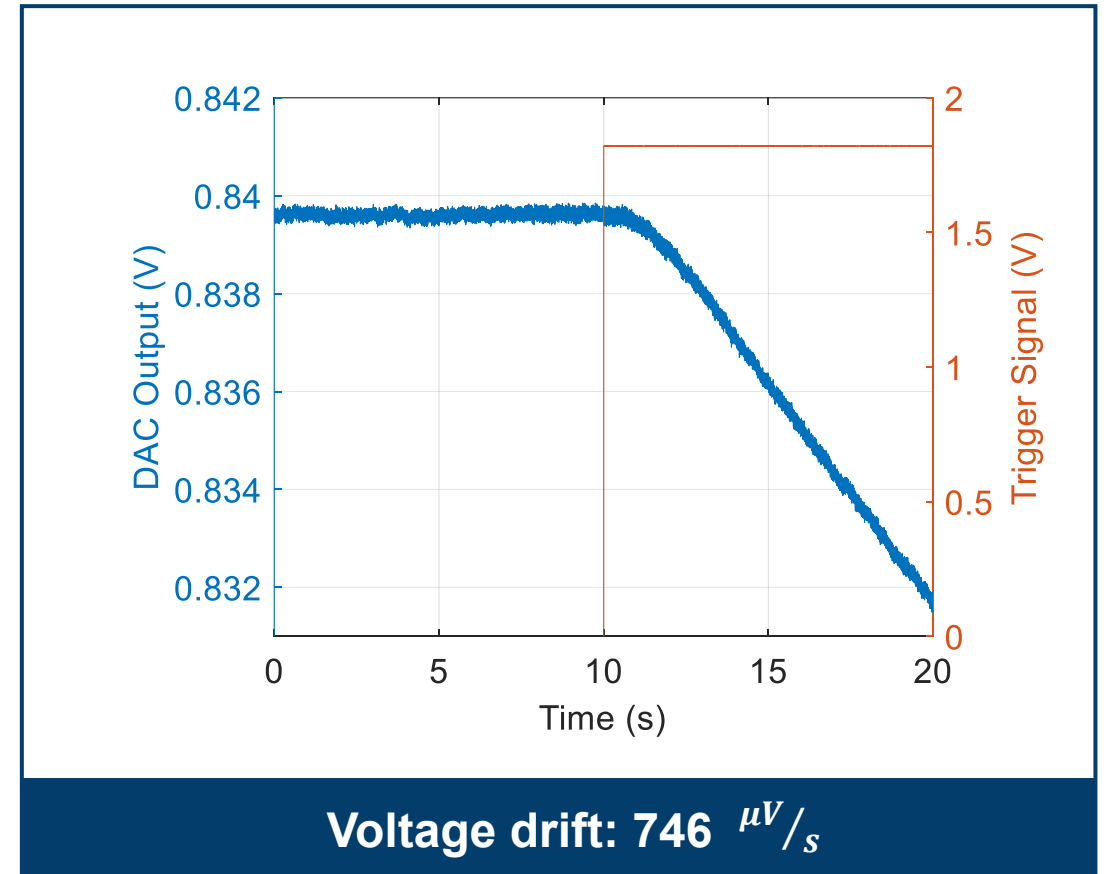
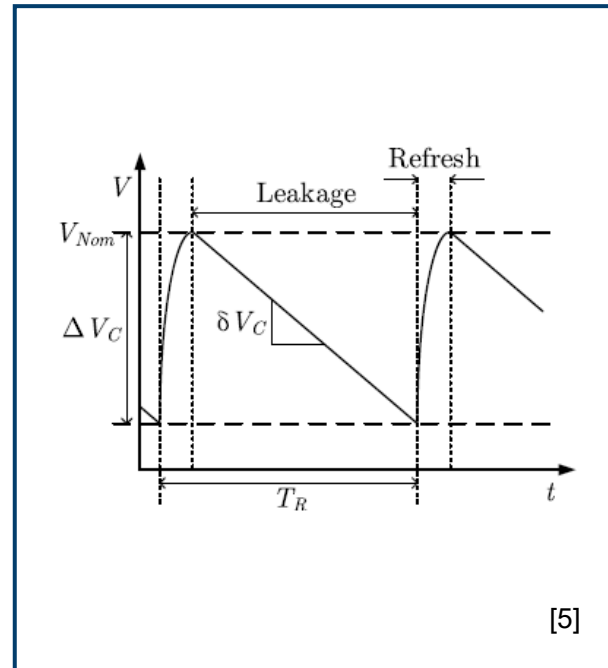
506 skipped input words → 11.81 Bit



MEASUREMENTS

Defined hold trigger for qubit operation between refresh

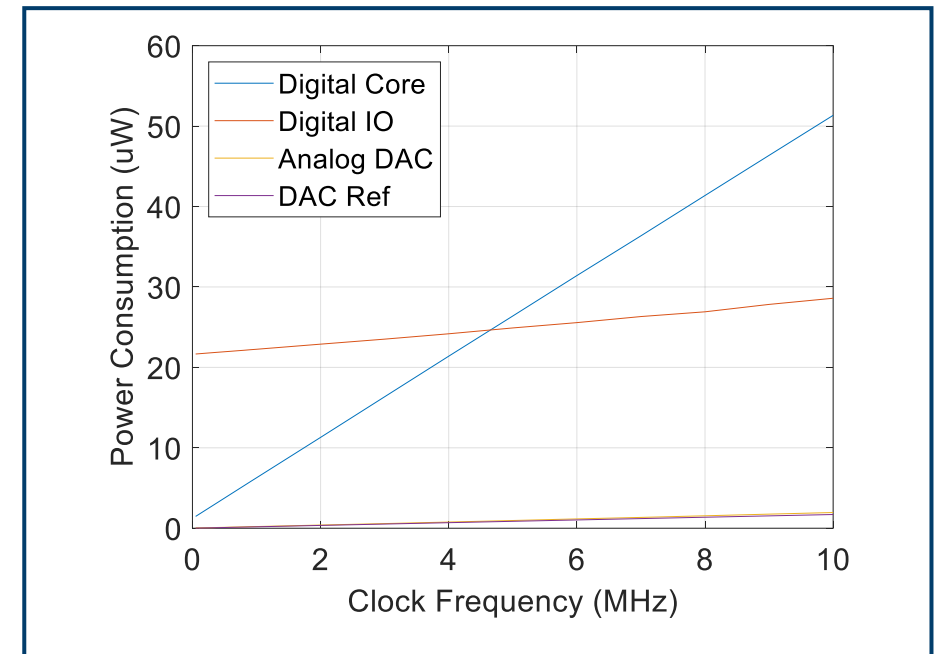
- Defined hold trigger for qubit operation between refresh
- Periodical refresh due to leakage in S&H channels
- Refresh increases noise at qubit gates
- Low temperature makes long hold time possible



DC BIAS

Power Consumption And Noise

Component	Power Consumption @ 5 MHz Clock
Analog DAC	0.96 μW
Analog DAC reference	0.86 μW
Analog DAC total	1.8 μW (152 nW per channel)
Digital IO	24.9 μW
Digital Core	26.4 μW
Total	53.1 μW

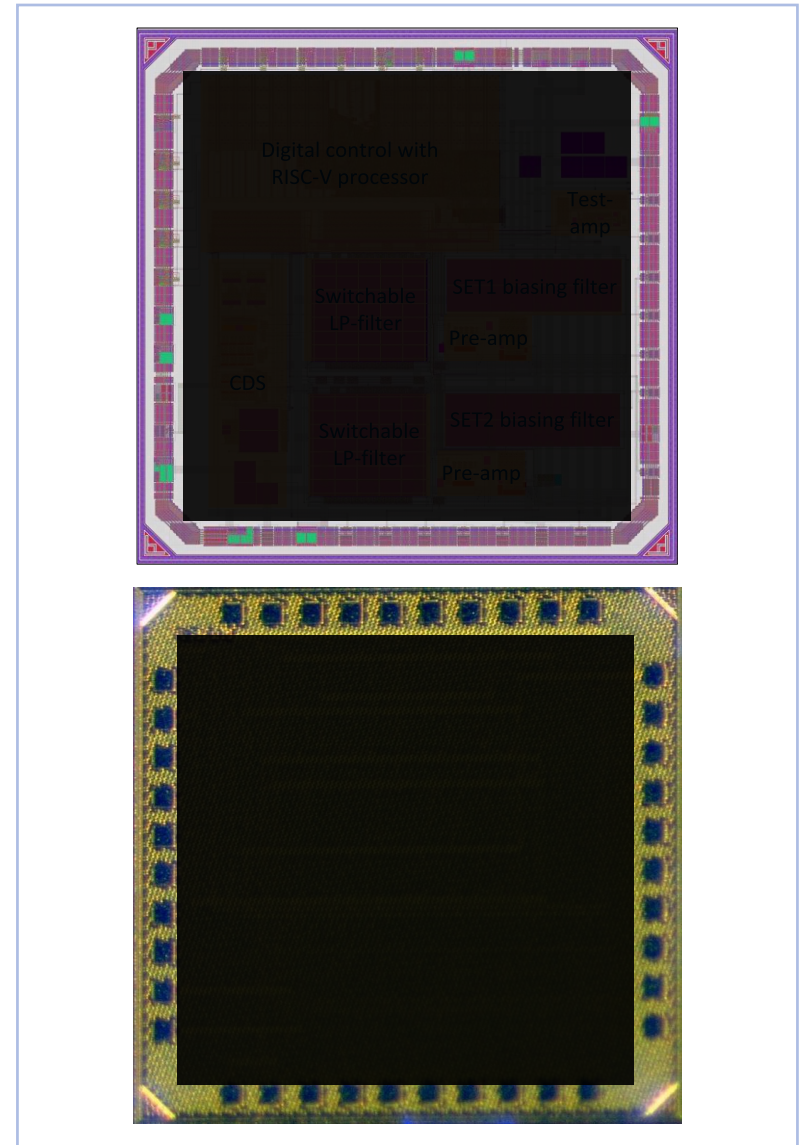


12 Channel running at 24 kHz channel refresh rate at 5 MHz Clock
Integrated noise added by DAC @ 1MHz Clock $\approx 119 \mu\text{V}_{\text{rms}}$

POWER DRAW IN PADFRAME

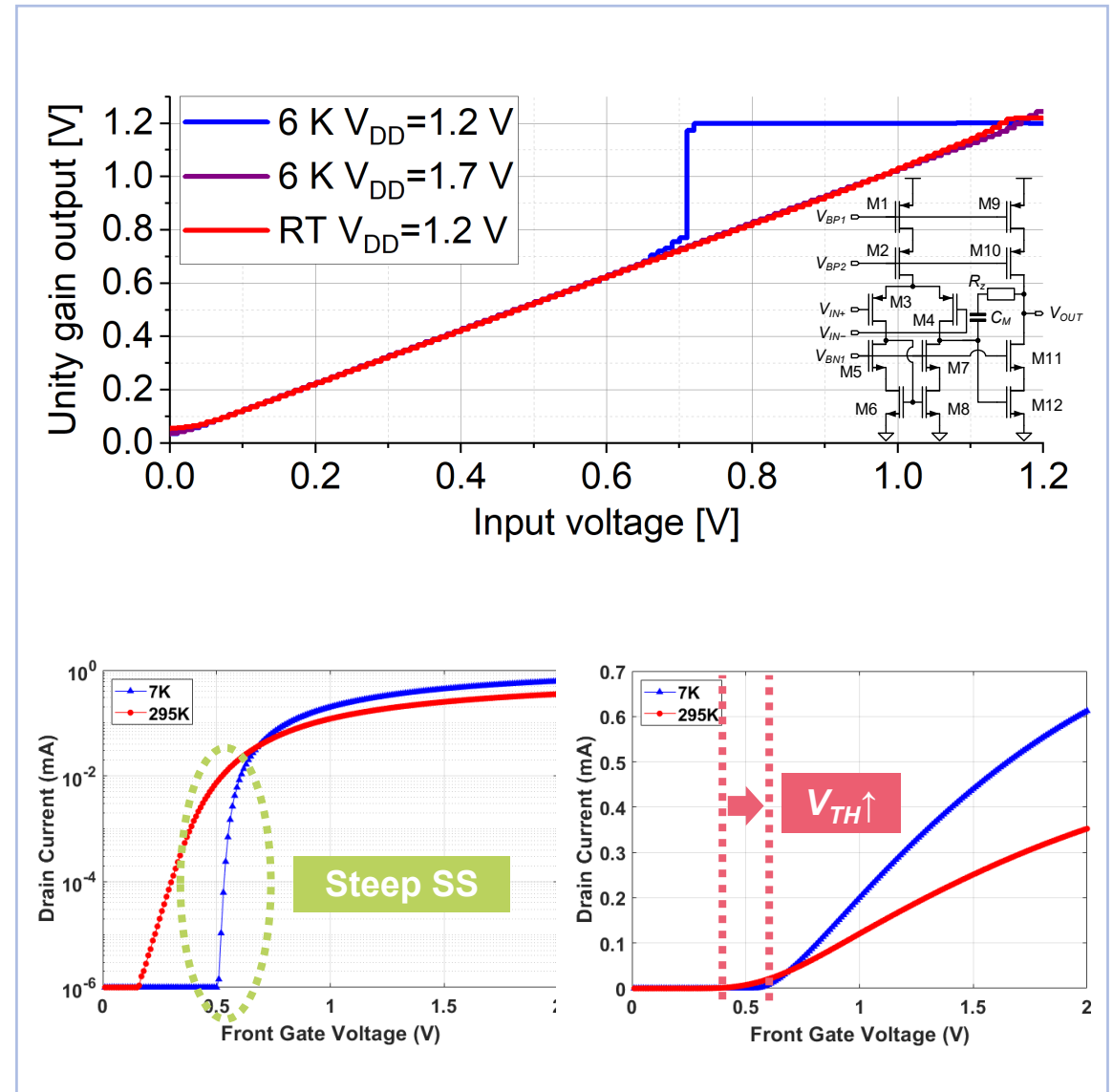
Padframe IP Considerations

- Padframe IP is not made for cryo. temperature
- **Analog pads** are good
 - Typically less leakage in ESD structures
- **Digital pads:**
 - Functionality (mostly fine)
 - even with complex internal circuitry
 - Power (every μW counts at mK)
 - Consider internal power OK generation
 - May generate internal bias voltages (e.g. for IO \leftrightarrow core voltage levelshifter)



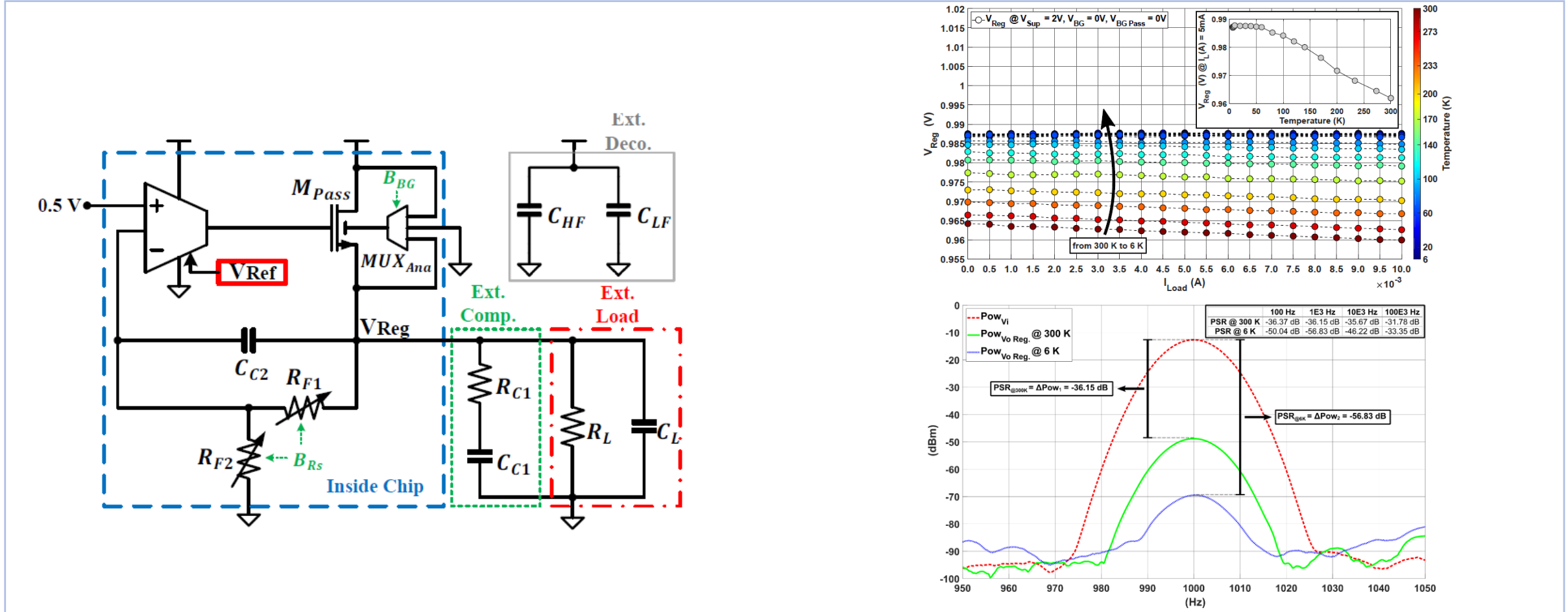
OPAMP

- Clipping of Opamp output at cryo temp.
 - Subthreshold operation problematic
 - Due to steep SS
- Increase supply for extra headroom
 - Use **low supply circuit topologies**
- **Pay extra attention to stay in strong inversion**
 - Compensate or be aware of V_{TH} shift



VOLTAGE REFERENCES

Voltage Reference and Regulator Circuit in 22nm FD-SOI

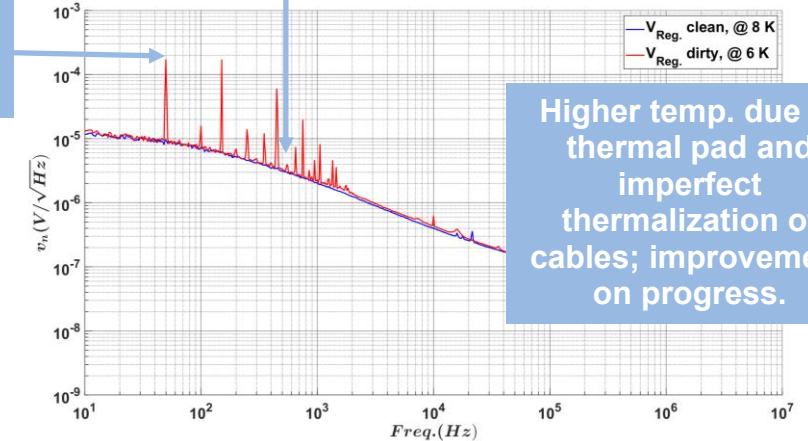
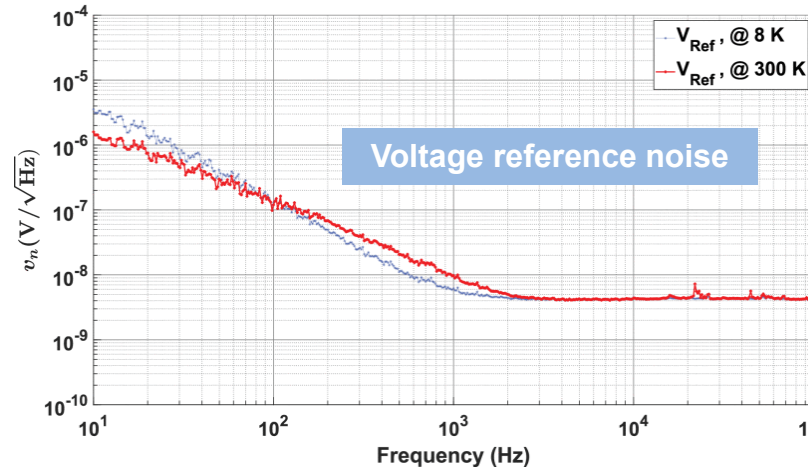
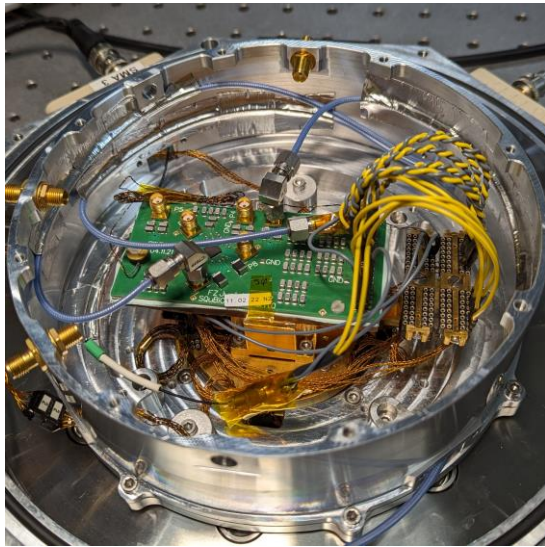


[2] A. R. Cabrera-Galicia, et.al, "Voltage Reference and Voltage Regulator for the Cryogenic Performance Evaluation of the 22nm FDSOI Technology," in IEEE Open Journal of Circuits and Systems, vol. 5, pp. 377-386, 2024, doi: 10.1109/OJCS.2024.3466395

NOISE

Cryostat and Voltage Reference & Regulator

- Avoid GND loops in the cryostat
 - Counteracting the wish to thermal couple
- Increased 1/f noise; decreased thermal noise



Ground loop noise is coupled to regulator output via cold plate.

Ground loop noise is removed by electrically detaching the regulator from the cold plate.

Higher temp. due to thermal pad and imperfect thermalization of cables; improvement on progress.

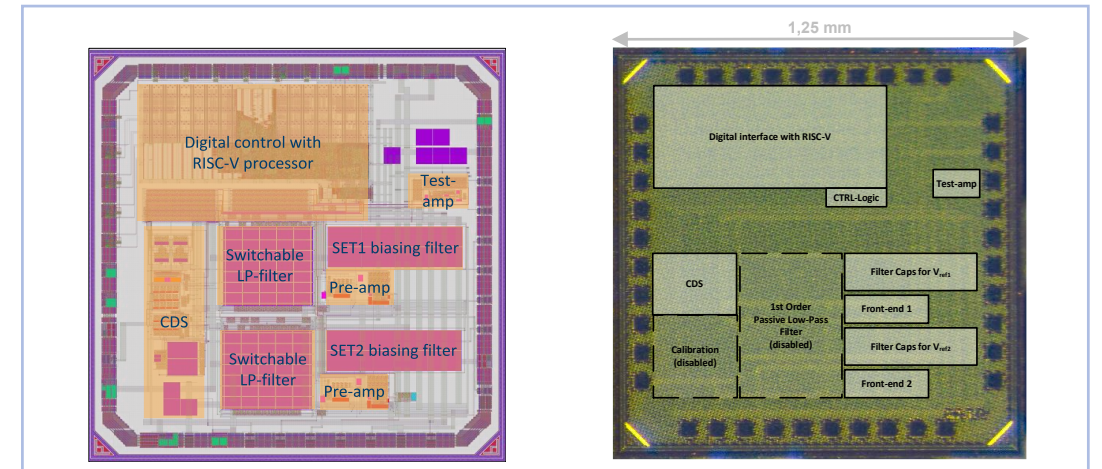
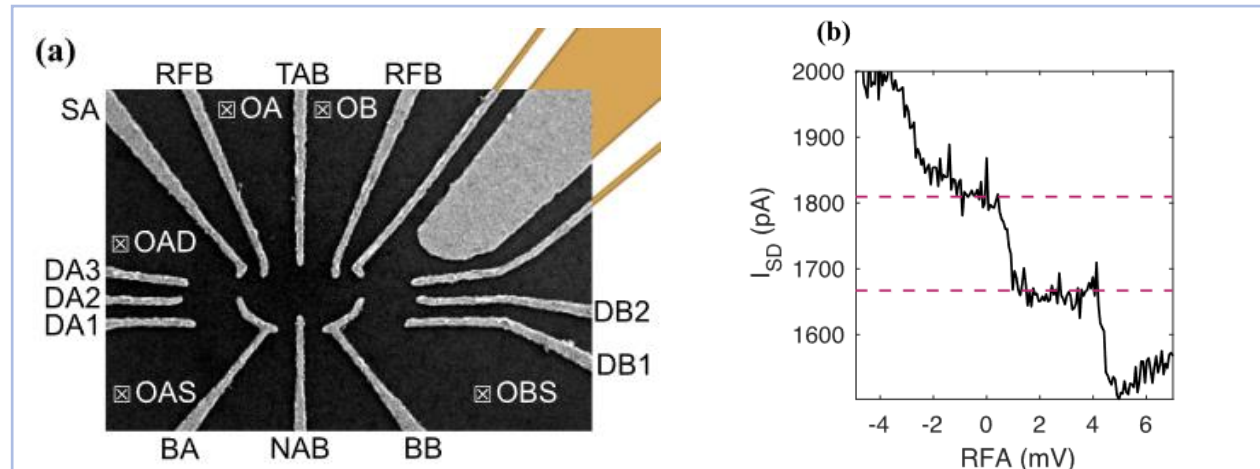
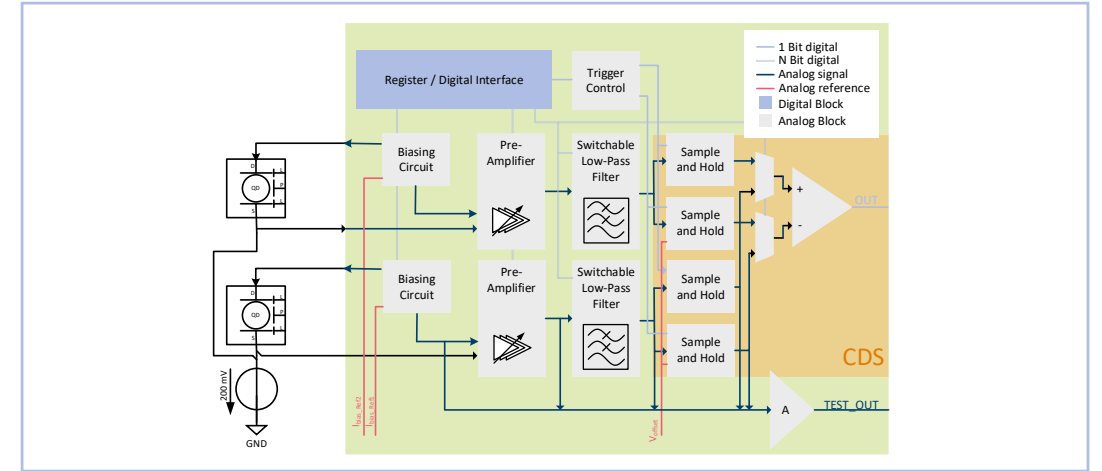
[2] A. R. Cabrera-Galicia, et.al, "Voltage Reference and Voltage Regulator for the Cryogenic Performance Evaluation of the 22nm FDSOI Technology," in IEEE Open Journal of Circuits and Systems, vol. 5, pp. 377-386, 2024, doi: 10.1109/OJCS.2024.3466395

QUBIT READOUT



Qubit Readout - QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots

- **Target: Current readout of quantum dots**
- Pauli spin blockade to convert spin to charge
- Single electron transistor (SET) to convert charge to current (signal ca. 250 pA)



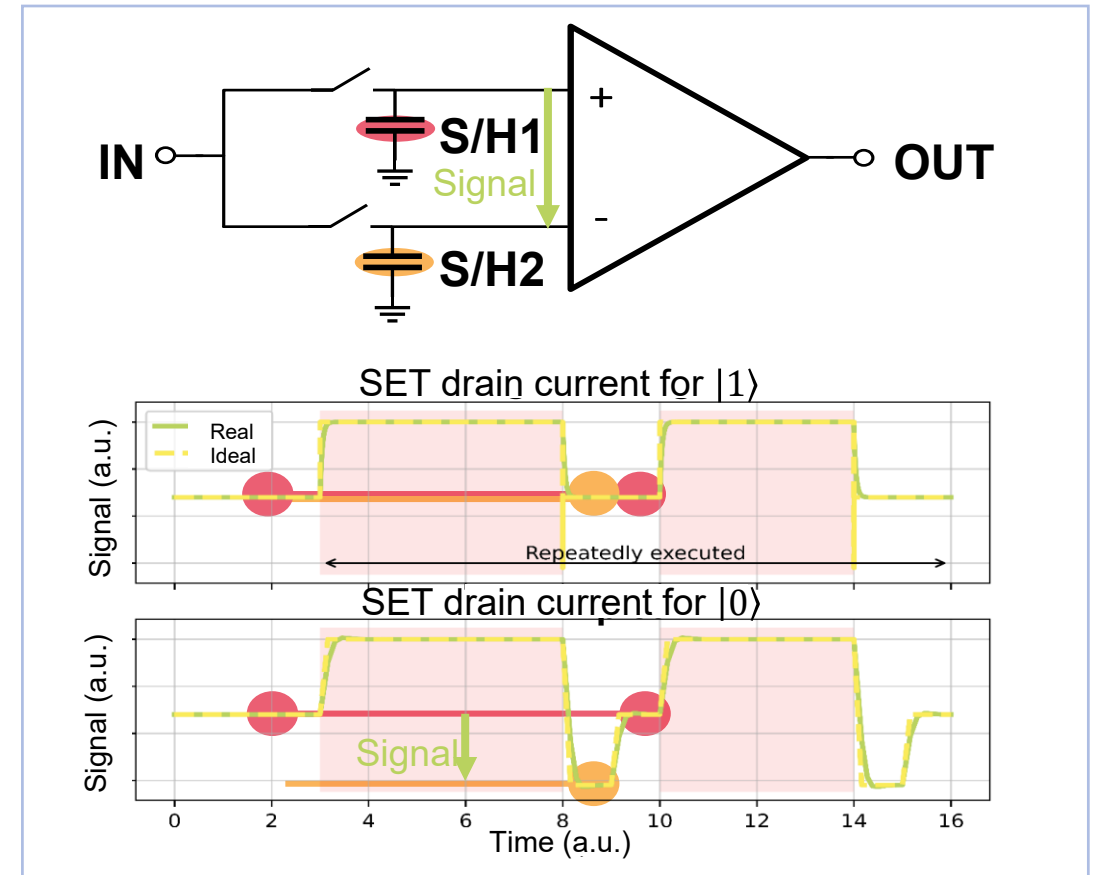
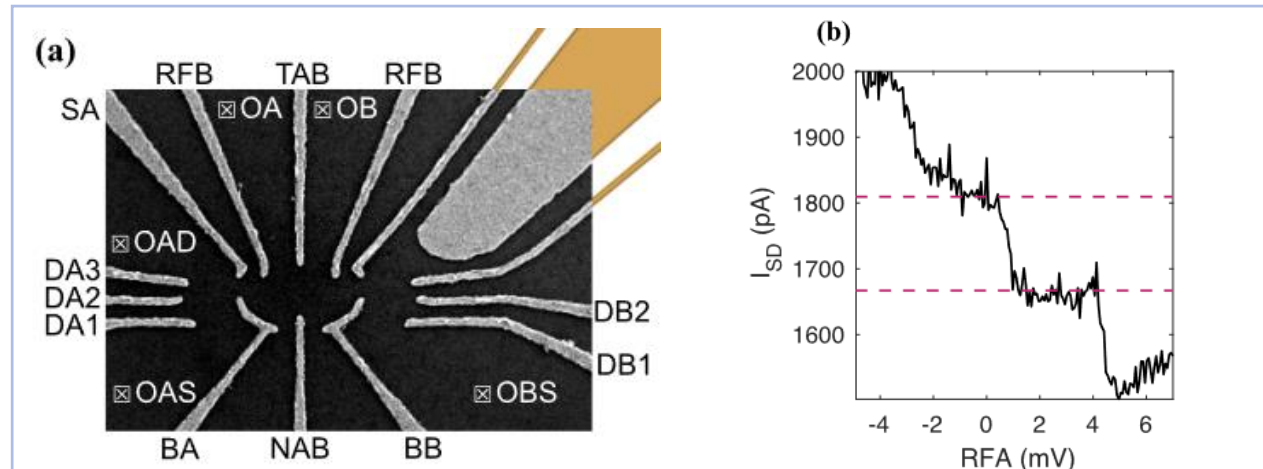
[3] J.Buehler et al., "QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots", Global Physics Summit 2025, MAR-G19/4
 [[10] Kammerloher, E. (2022) Improving the output signal of charge readout for quantum computing in electrostatically defined quantum dots with a new sensing dot concept.

QUBIT READOUT



Qubit Readout - QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots

- **Correlated Double Sampling (CDS)**
 - 1st sample after qubit initialization
 - 2nd sample after qubit operation
 - Cancellation of low frequency noise



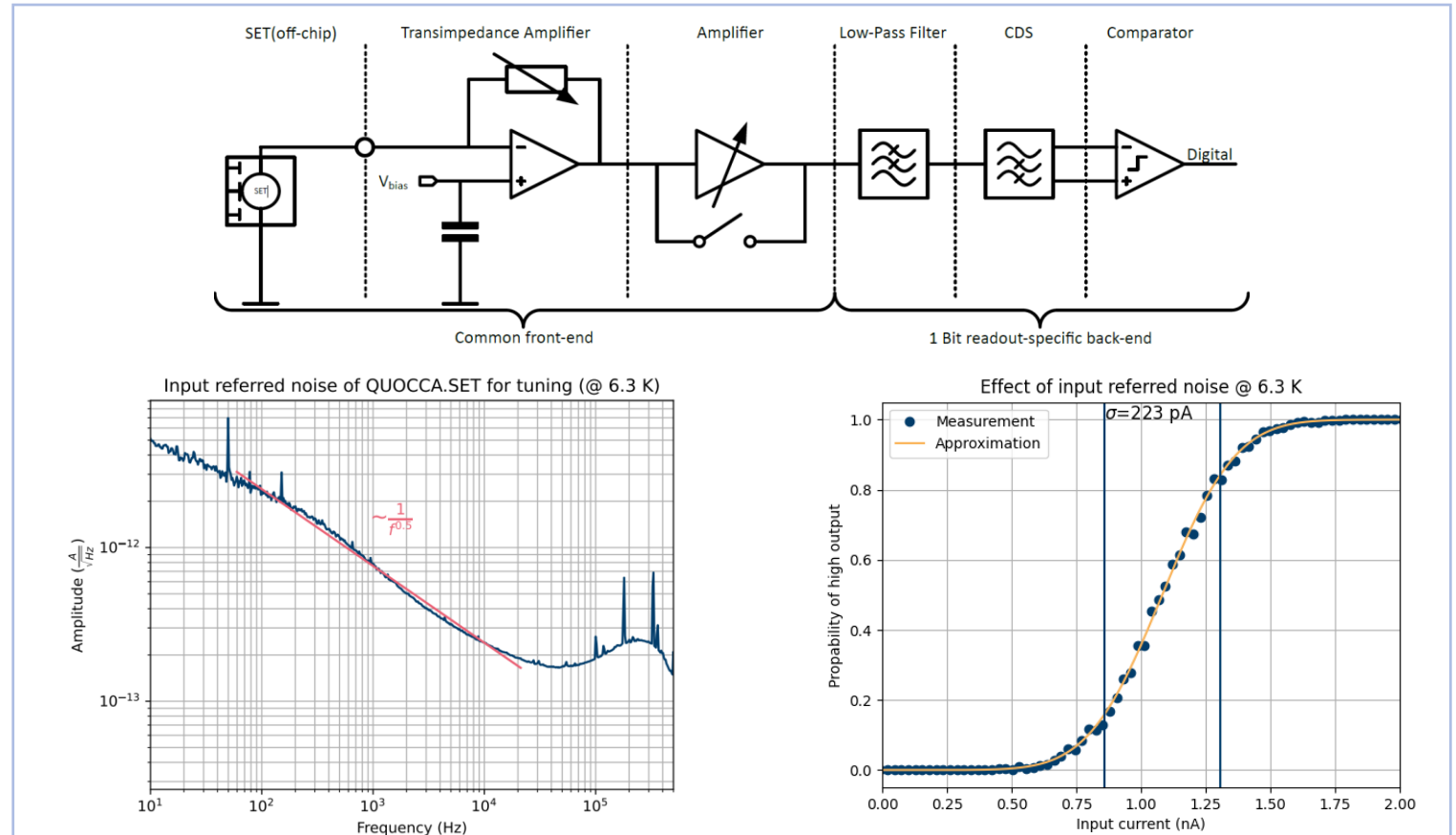
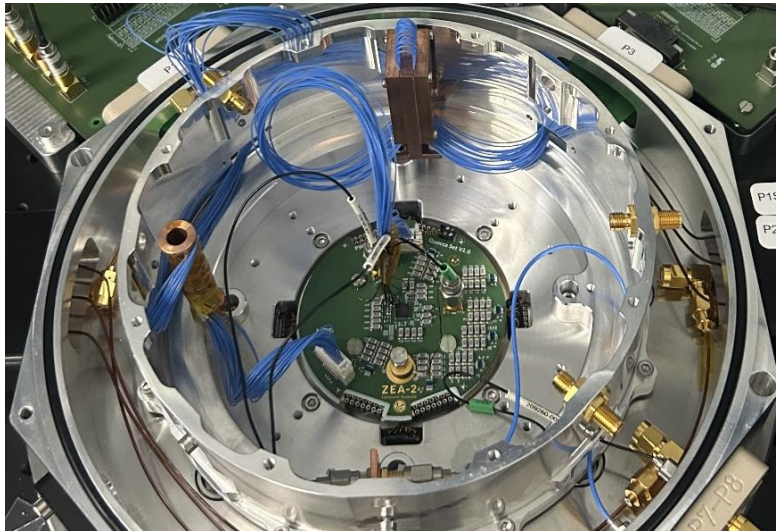
[3] J.Buehler et al., "QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots", Global Physics Summit 2025, MAR-G19/4

QUBIT READOUT



Qubit Readout - QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots

- 223 pA RMS @ 1 μ s, max. BW
- 111 pA RMS @ 1 μ s, 1 kHz BW
- Digital Power: 41 μ W
- Analog Power: 33.6 μ W/SET



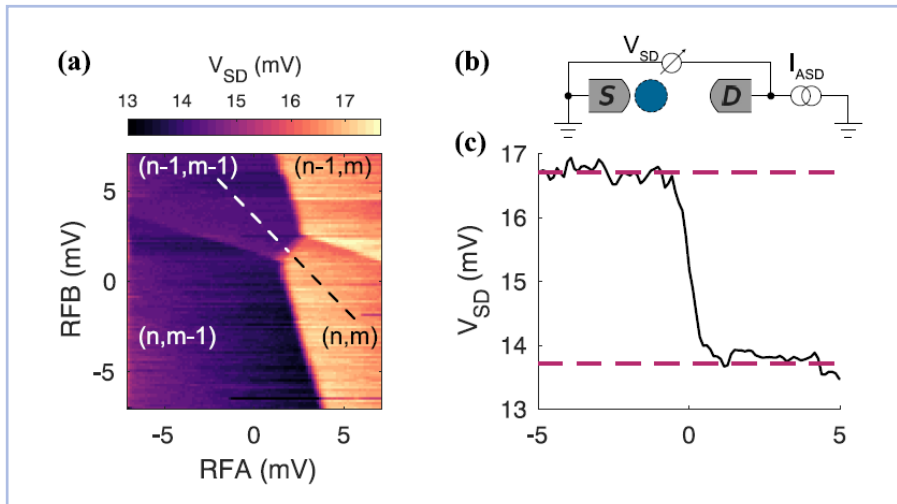
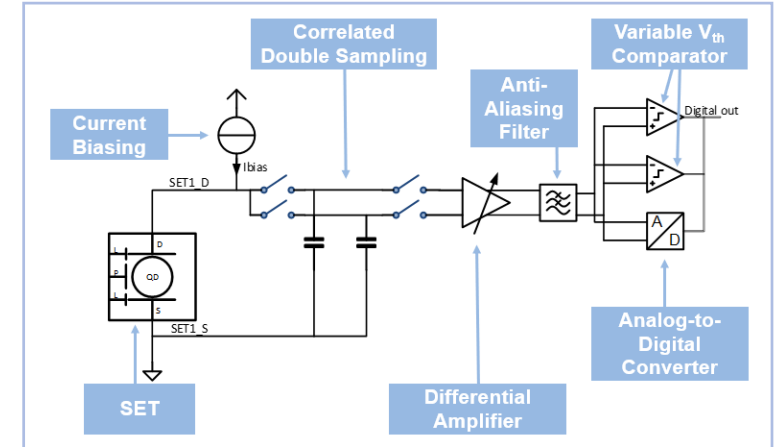
[3] J.Buehler et al., "QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots", Global Physics Summit 2025, MAR-G19/4

QUBIT READOUT



Qubit Readout - QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots

- **Target: Voltage readout of quantum dots**
- Pauli spin blockade to convert spin to charge
- Single electron transistor to convert charge to voltage
- Signal: ≈ 3 mV [5]



Digital	Front-End	
<ul style="list-style-type: none"> • Triggered FSM • JTAG and UART 	Back-End	
Biasing	<ul style="list-style-type: none"> • S/H with variable Capacitances 	
<ul style="list-style-type: none"> • Current-mirror bank 	<ul style="list-style-type: none"> • Dynamic Comparator • 7 bit SAR ADC 	

[4] J.Buehler et al., "Scalable integrated readout of semiconductor quantum dots using current biasing", Global Physics Summit 2026

<https://summit.aps.org/smt/2026/events/MAR-Z17/15>

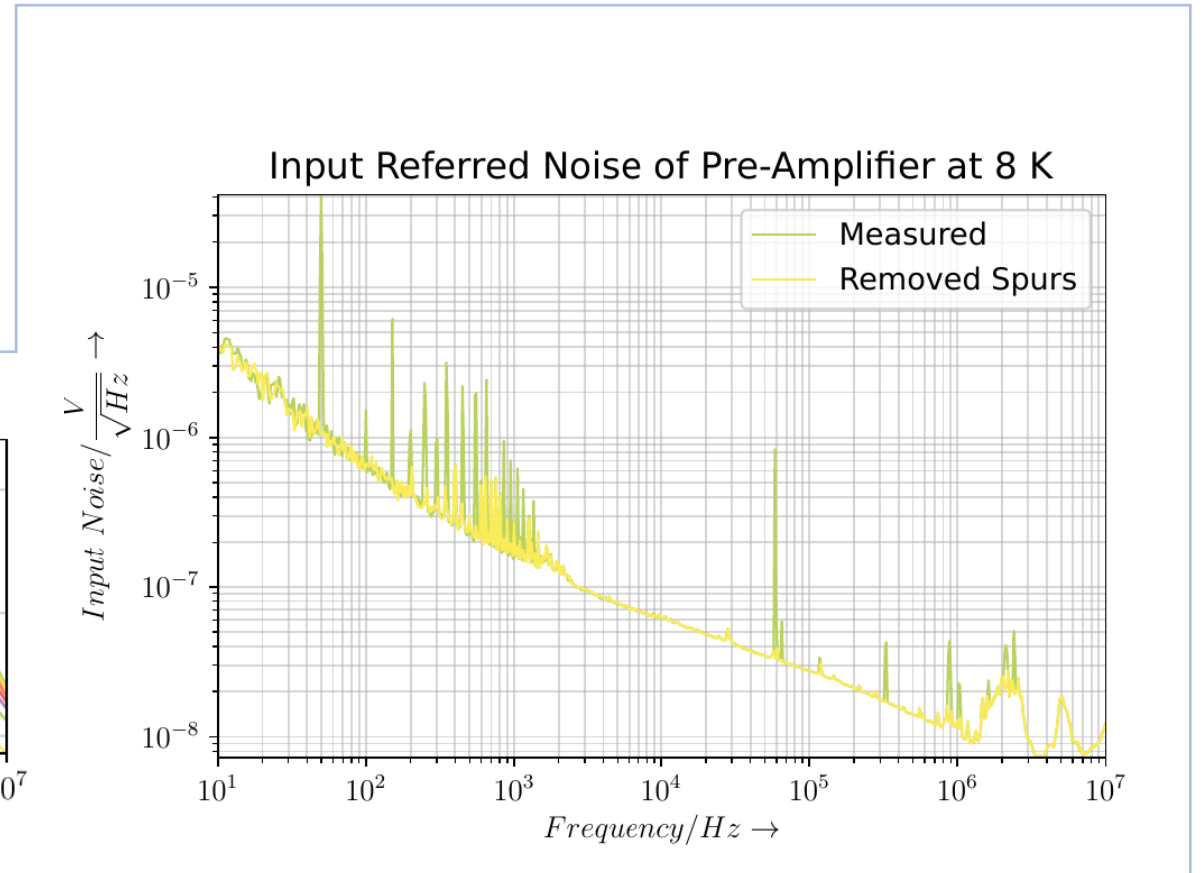
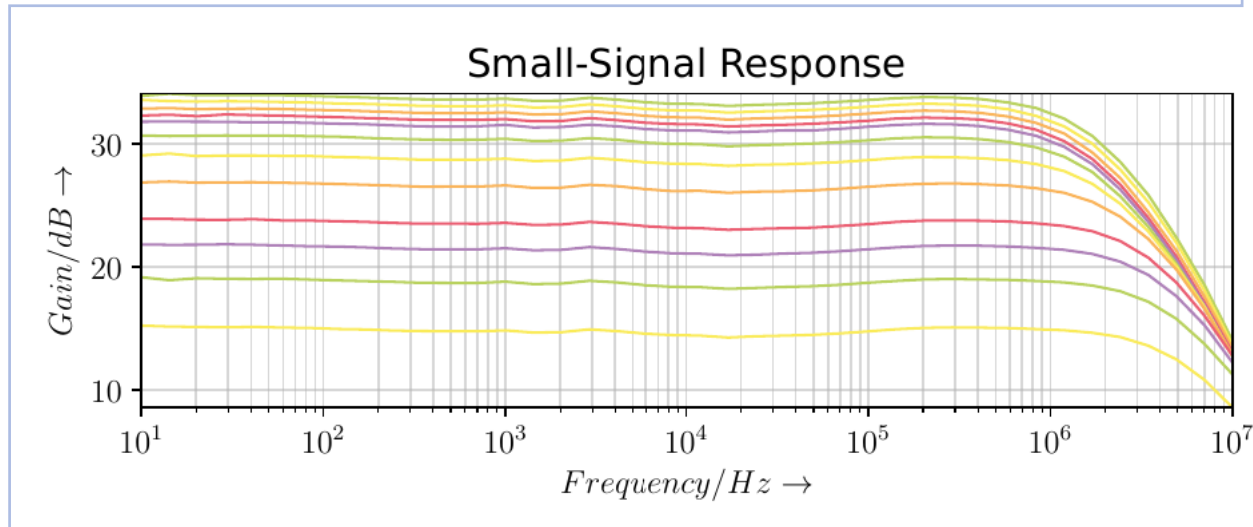
[10] Kammerloher, E. (2022) Improving the output signal of charge readout for quantum computing in electrostatically defined quantum dots

QUBIT READOUT

Amplifier Measurements at 8 K



- Power: $\approx 57 \mu\text{W}$
- Gain: $\approx 8 - 45 \text{ dB}$
- Bandwidth: $\approx 1.5 - 5.5 \text{ MHz}$
- Active area: $\approx 1500 \mu\text{m}^2$



[4] J.Buehler et al., "Scalable integrated readout of semiconductor quantum dots using current biasing", Global Physics Summit 2026
<https://summit.aps.org/smt/2026/events/MAR-Z17/15>

QUBIT READOUT

Performance of 1-Bit readout

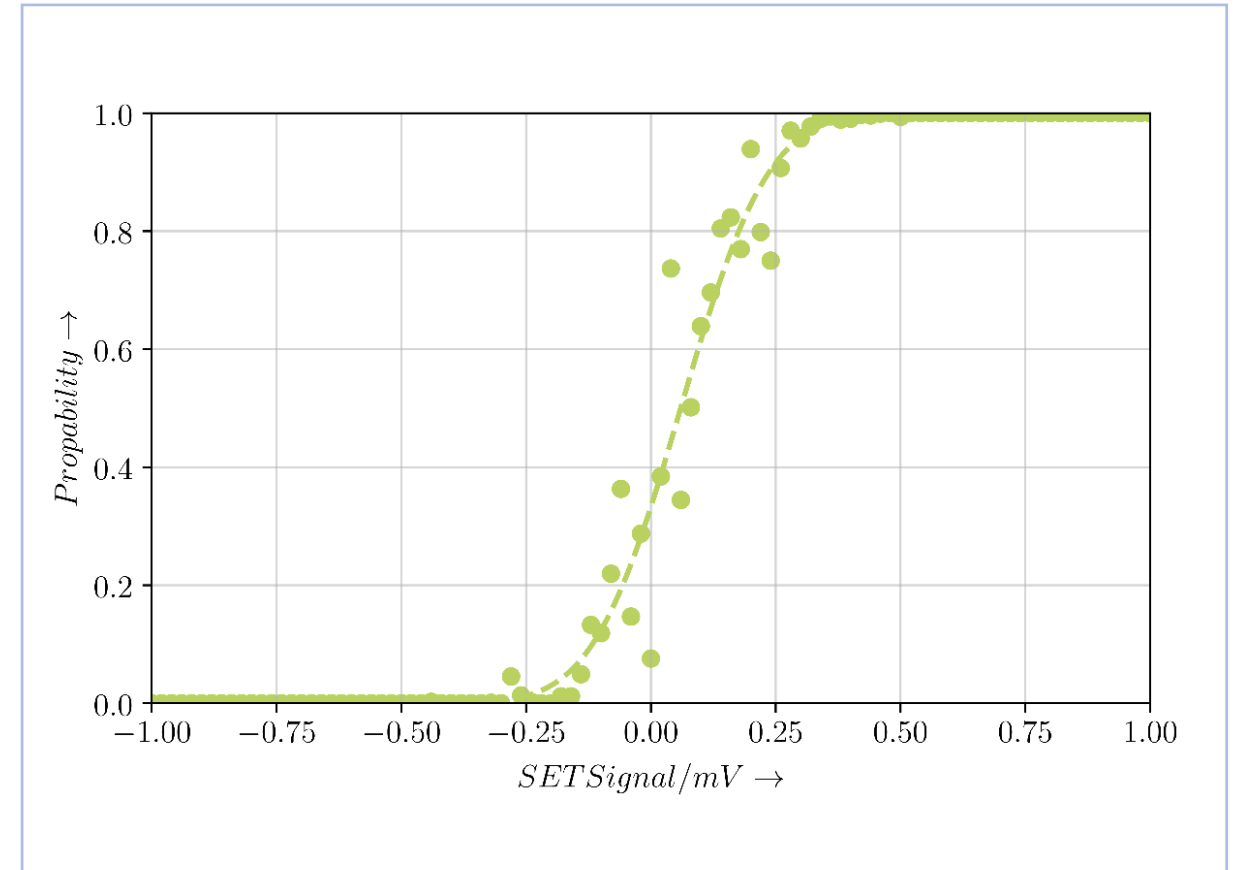
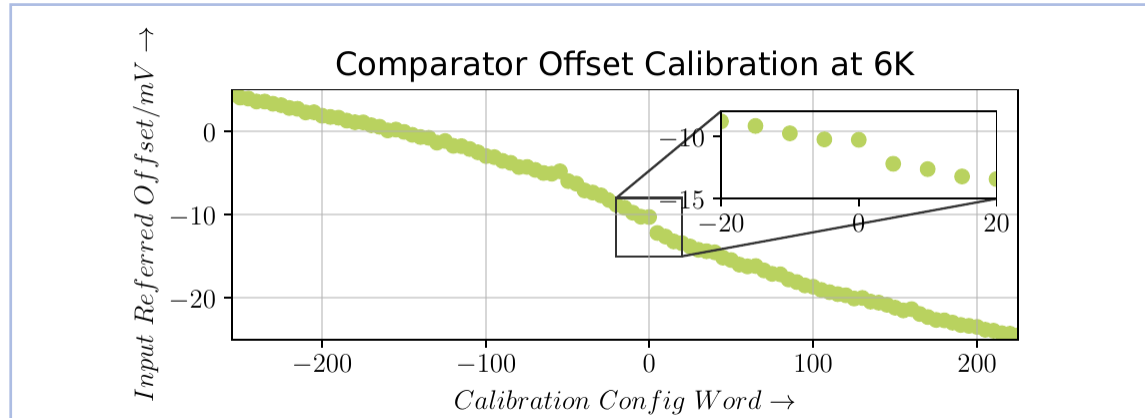


500 ns Sampling Time

- 138 μV RMS @ $C_{\text{sample}} \approx 20$ pF
- 318 μV RMS @ $C_{\text{sample}} \approx 0,2$ pF

Power:

- Digital Power: 8.5 μW
- Analog Power: 115 μW

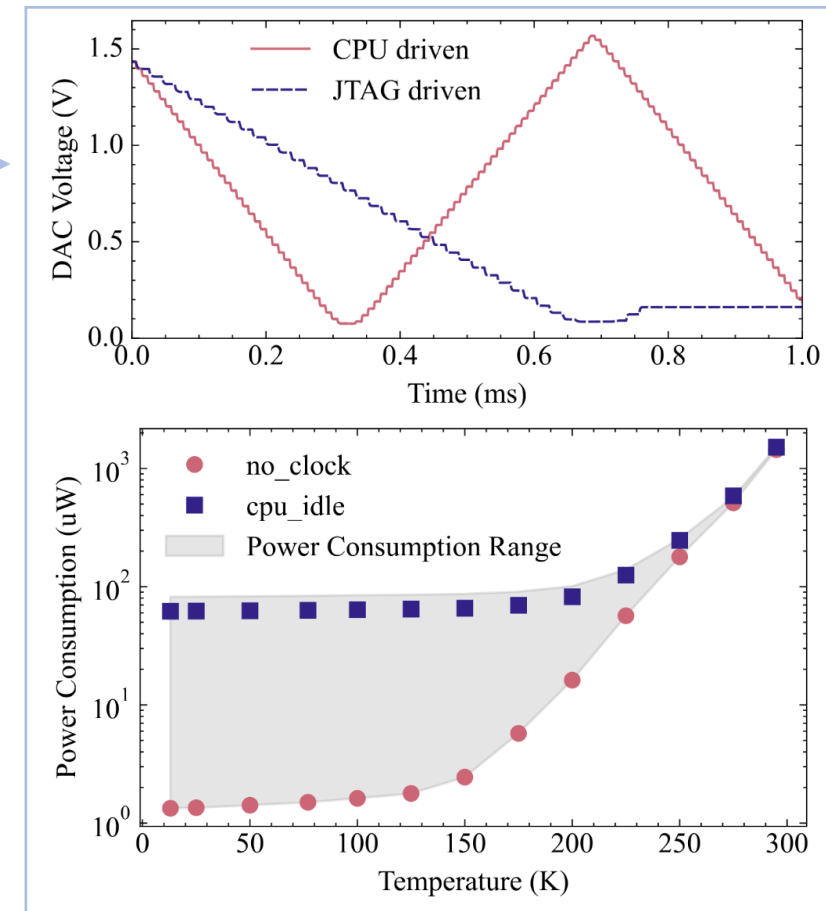
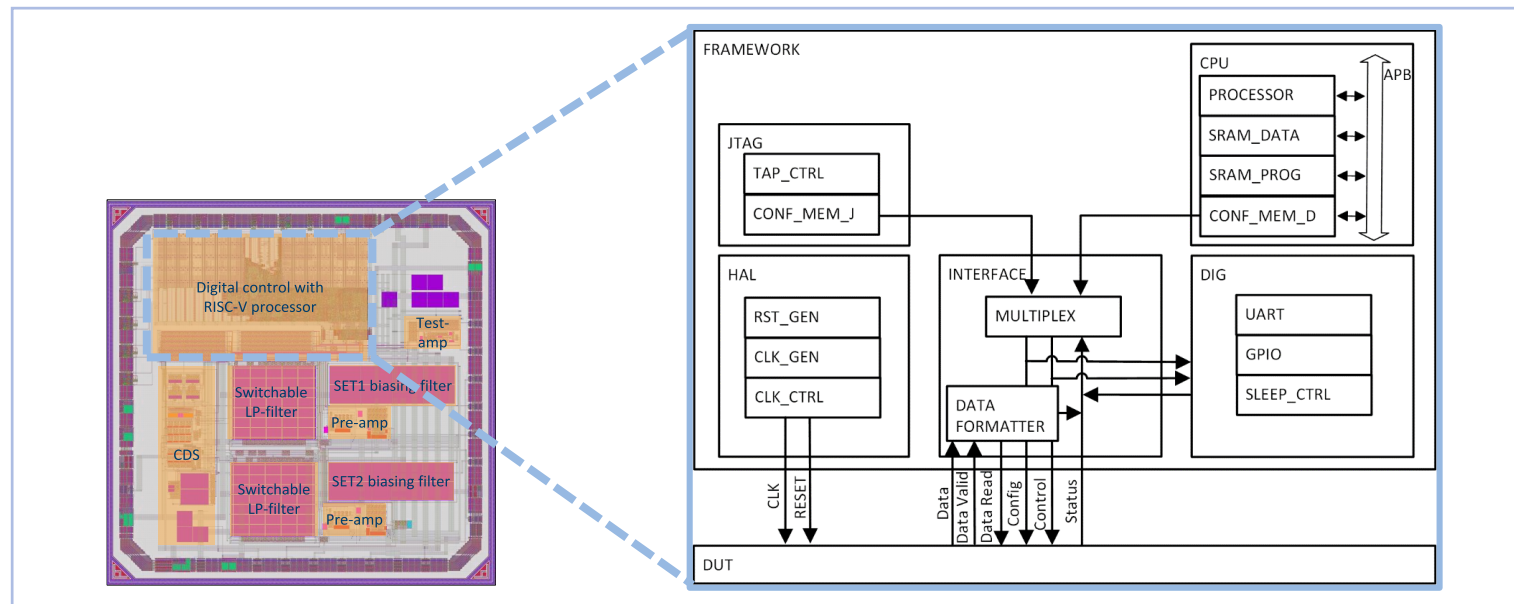


INTEGRATED RISC-V

Rapid Prototyping Platform for Integrated Circuits for Quantum Computing



- RISC-V with SRAM and APB
- Enables flexibility in control (algorithms)
- Leakage negligible at cryo



[5] J. Mair et al., "Rapid Prototyping Platform for Integrated Circuits for Quantum Computing," 2024 20th International Conference on Synthesis, Modeling, Analysis and Simulation Methods and Applications to Circuit Design (SMACD), Volos, Greece, 2024, pp. 1-4, doi: 10.1109/SMACD61181.2024.10745395.

DIGITAL INTERFACE

Comparison of Industry Standard Protocols

Protocol	Pro 😊	Cons ☹️
UART	2-wire interface (RX TX) No pull-up/down	Requires sync.
I ² C	2-wire interface (SDA SCL)	Pull-ups
SPI	No pull-up/down	3[4]-wire interface (SCLK MOSI MISO [CE])
JTAG	No pull-up/down	4-wire interface (TCK TMS TDI TDO) Complex state-machine
cJTAG	2-wire interface (TCKC TMSC)	Complex state-machine Less established Optional Pull-ups/downs

- Write & read IC config regs
- Configuration of IC blocks



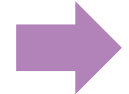
CRYOGENIC CO-INTEGRATION



Multiple Approaches

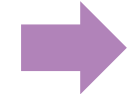
IC and Qubit:
Same Interposer

Electron Temperature
Qubit: ca. 2-3K



IC and Qubit:
Two Interposer

Electron Temperature
Qubit: ca. 0.5-1K



IC and Qubit:
Direct Copper

Electron Temperature
Qubit: < 0.4K

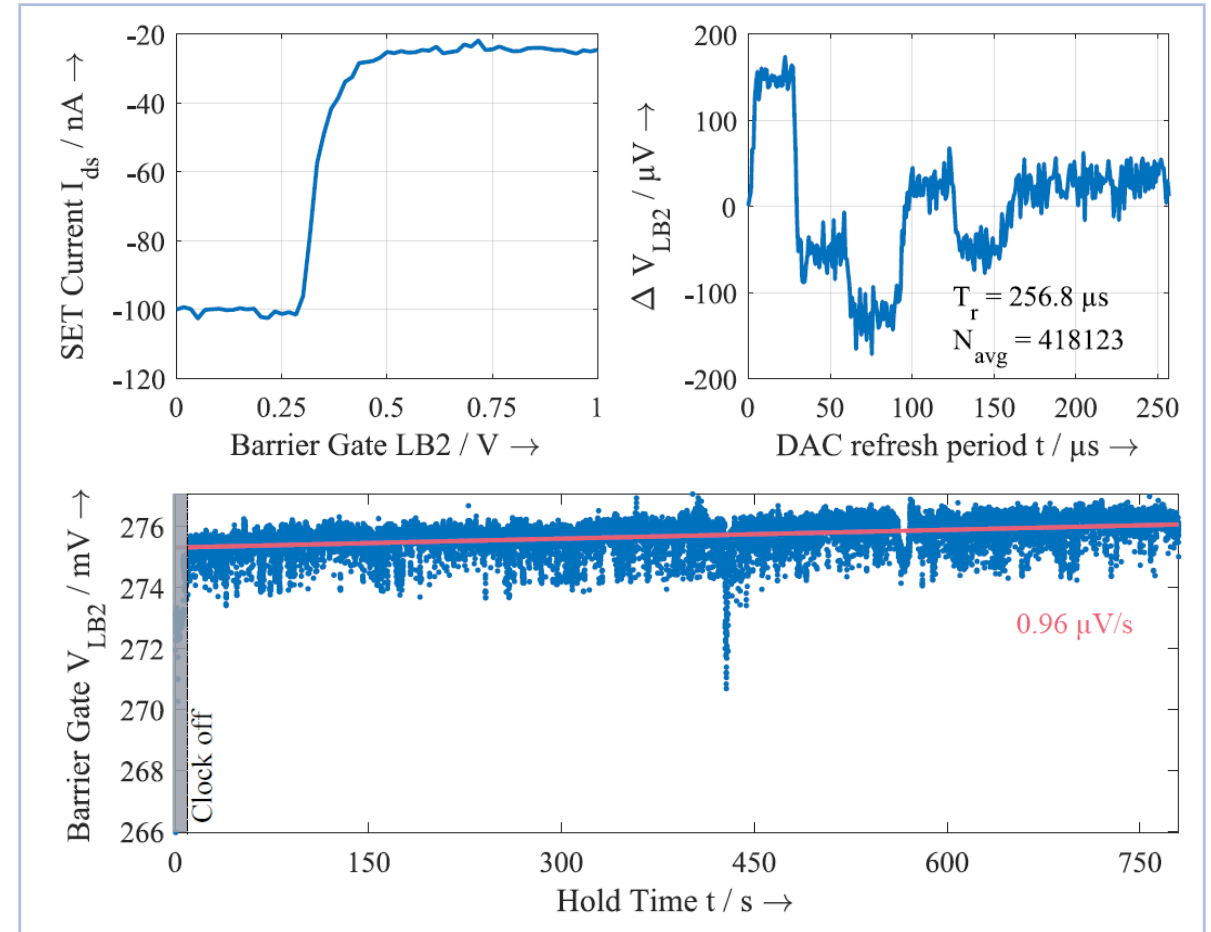
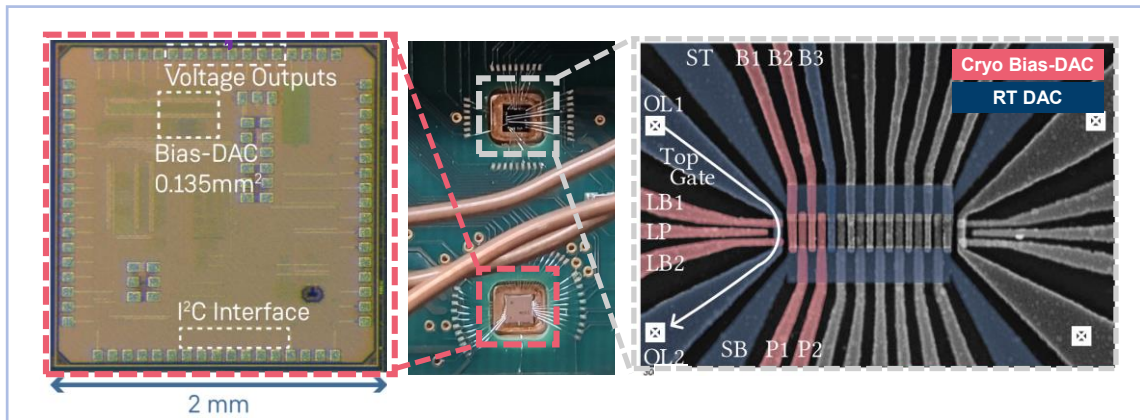
[6] L. Schreckenberget al., "SiGe Qubit Biasing with a Cryogenic CMOS DAC at mK Temperature," ESSCIRC 2023

CRYOGENIC CO-INTEGRATION



Ultra-low Leakage Currents

- Bias DAC cycling through 7 metal electrodes
 - SET used as measurement amplifier
 - Visible cross-talk depending on location
- Leakage rates on metal electrodes meas.
 - 2 pF on-chip cap.; ca. 300 fF off-chip cap.
 - Ultra-low voltage drift of $<1 \mu\text{V/s}$



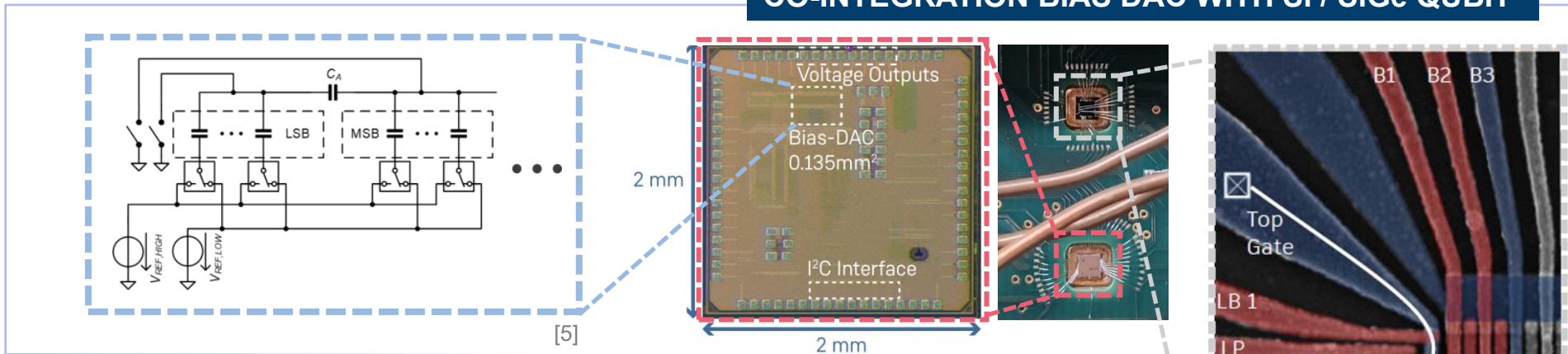
[6] L. Schreckenberget al., "SiGe Qubit Biasing with a Cryogenic CMOS DAC at mK Temperature," ESSCIRC 2023

CRYOGENIC CO-INTEGRATION

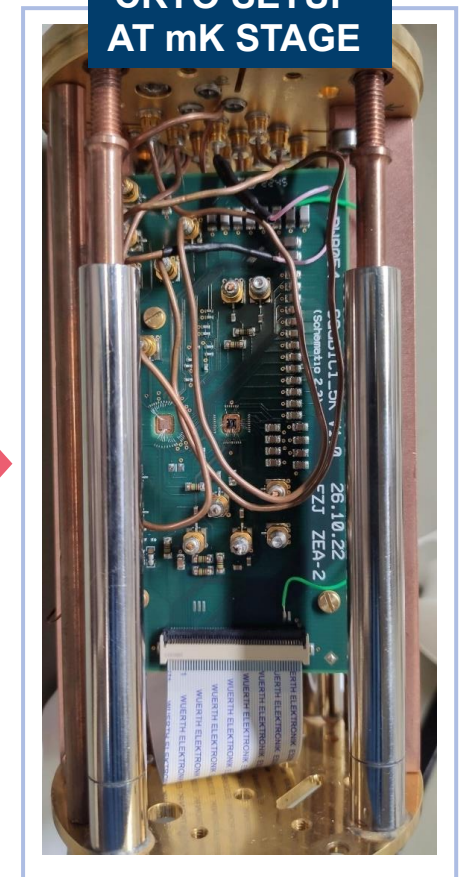
Qubit DC Biasing



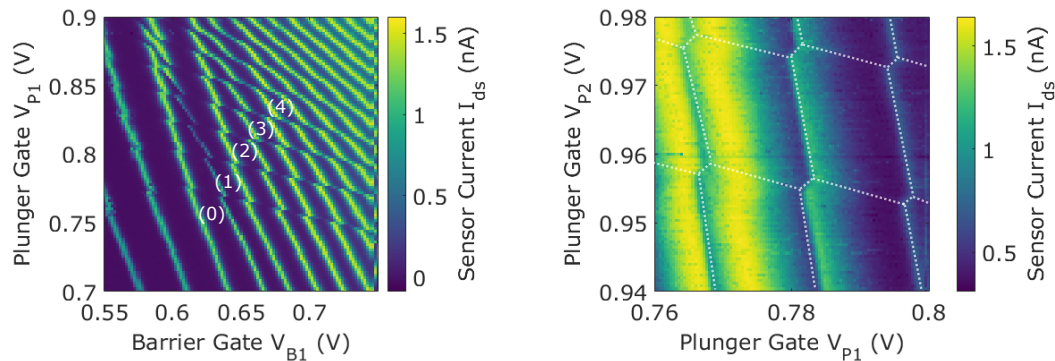
CO-INTEGRATION BIAS DAC WITH Si / SiGe QUBIT



CRYO SETUP AT mK STAGE



CHARGE SENSING OF SINGLE AND DOUBLE QUANTUM DOT



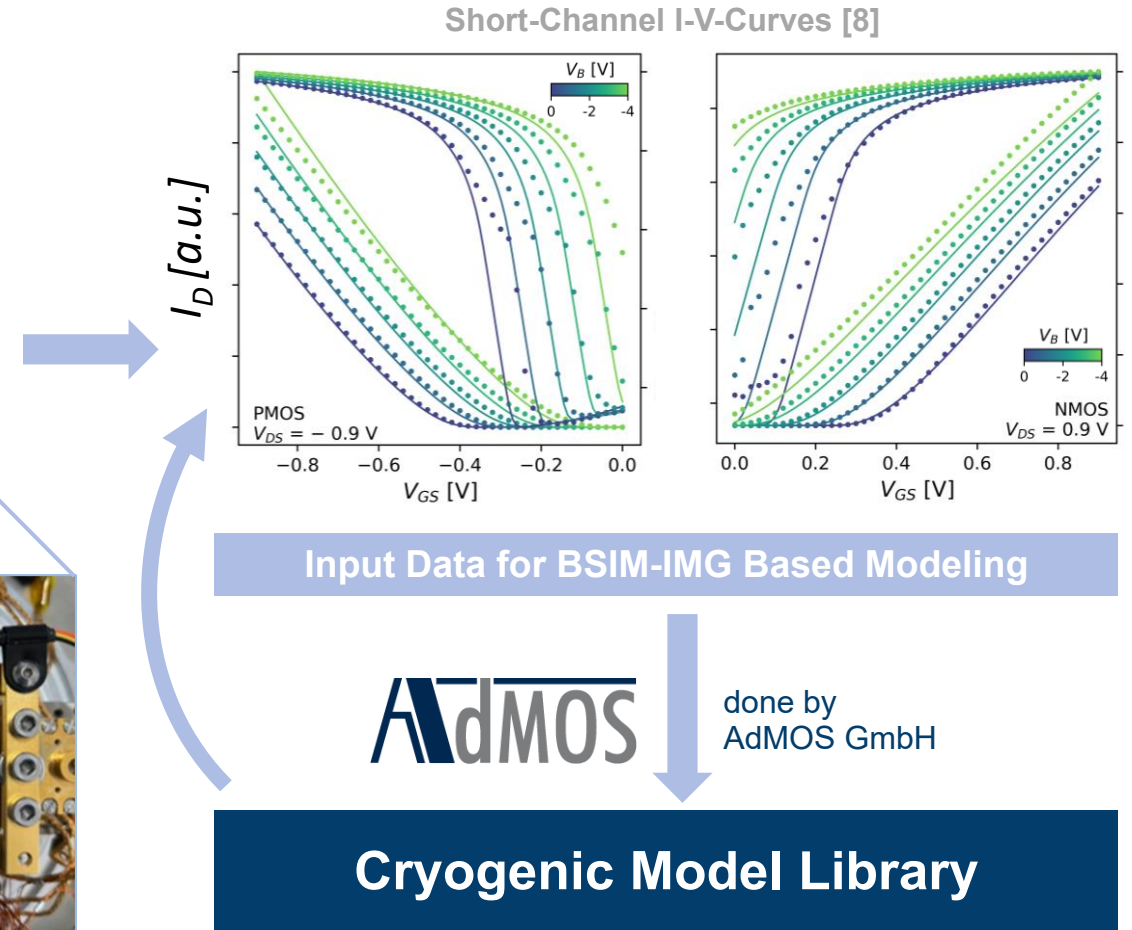
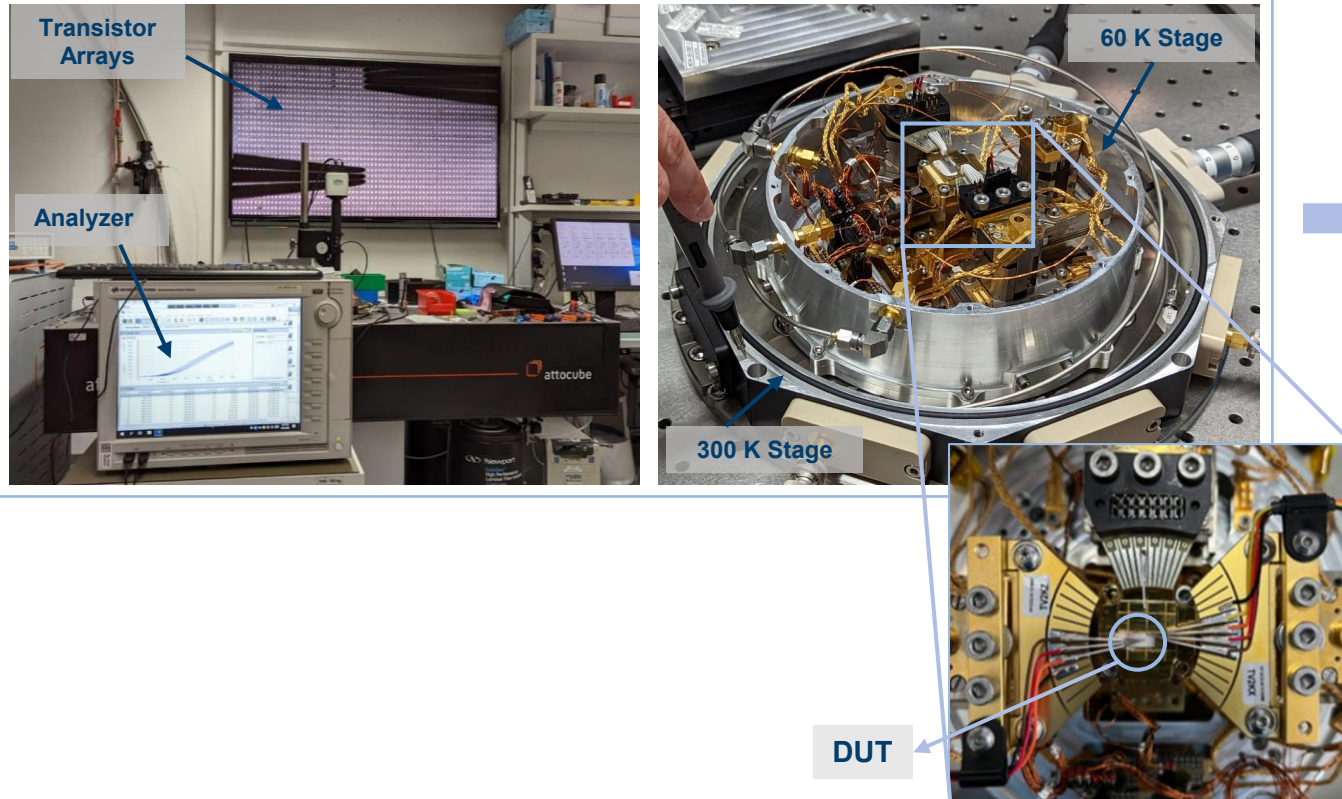
[7] P. Vliex et al., "Bias Voltage DAC Operating at Cryogenic Temperatures for Solid-State Qubit Applications," IEEE Solid-State Circuits Letters, 2020
 [6] L. Schreckenberget al., "SiGe Qubit Biasing with a Cryogenic CMOS DAC at mK Temperature," ESSCIRC 2023

CRYOGENIC MEASUREMENTS

Inputs for a Cryo-PDK for 22 nm CMOS



Setup @ ICA | FZJ: $T_{\min} \sim 7\text{ K}$



[8] Chava, Phanish, et al. "Evaluation of cryogenic models for FDSOI CMOS transistors." 16th IEEE Workshop on Low Temperature electronics. No. FZJ-2024-05369. Zentralinstitut für Elektronik, 2024.

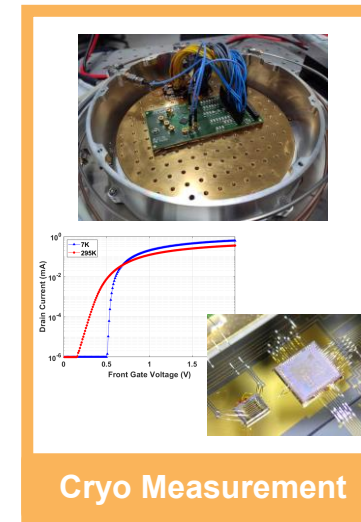
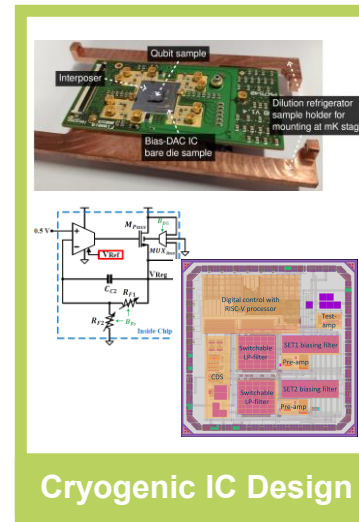
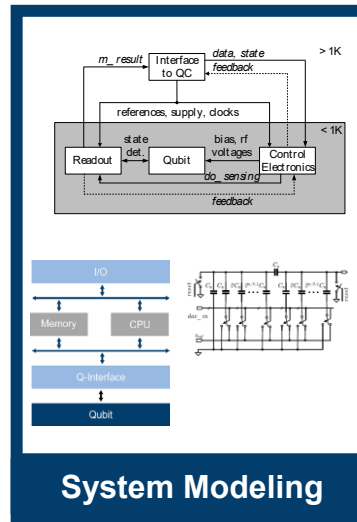
The QSolid project acknowledges the support of the Federal Ministry of Education and Research (BMBF) within the framework programme "Quantum technologies – from basic research to market" (Grant No. 13N16149).

SUMMARY

- Cryo-CMOS readout shown with current and voltage biasing.
- DC qubit biasing demonstrated in 22 nm and 65 nm, at cryo and with qubits

Cryogenic Pitfalls:

- Hidden IP power
- Cryo model shifts
- Ground loops in the cryostat
- Steep subthreshold slope
- Thermal anchoring



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Current Vacancies:



www.ica.fz-juelich.de

LinkedIn:



www.linkedin.com/showcase/ica-pgi4

Mastodon:



https://social.fz-juelich.de/@fzj_ica

Threads:



www.threads.com/@fzj_ica

REFERENCES

- [1] H. Banba et al. "A CMOS bandgap reference circuit with sub-1-V operation". In: IEEE Journal of Solid-State Circuits 34.5 (May 1999), pp. 670–674. doi: 10.1109/4.760378.
- [2] A. R. Cabrera-Galicia, et.al, "Voltage Reference and Voltage Regulator for the Cryogenic Performance Evaluation of the 22nm FDSOI Technology," in IEEE Open Journal of Circuits and Systems, vol. 5, pp. 377-386, 2024, doi: 10.1109/OJCAS.2024.3466395
- [3] J.Buehler et al., "QUOCCA.SET: A Scalable Readout IC for Semiconductor Quantum Dots", Global Physics Summit 2025, MAR-G19/4
- [4] J.Buehler et al., "Scalable integrated readout of semiconductor quantum dots using current biasinG", Global Physics Summit 2026 <https://summit.aps.org/smt/2026/events/MAR-Z17/15>
- [5] J. Mair et al., "Rapid Prototyping Platform for Integrated Circuits for Quantum Computing," 2024 20th International Conference on Synthesis, Modeling, Analysis and Simulation Methods and Applications to Circuit Design (SMACD), Volos, Greece, 2024, pp. 1-4, doi: 10.1109/SMACD61181.2024.10745395.
- [6] L. Schreckenbergr et al., "SiGe Qubit Biasing with a Cryogenic CMOS DAC at mK Temperature," ESSCIRC 2023
- [7] P. Vliex et al., "Bias Voltage DAC Operating at Cryogenic Temperatures for Solid-State Qubit Applications," IEEE Solid-State Circuits Letters, 2020
- [8] Chava, Phanish, et al. "Evaluation of cryogenic models for FDSOI CMOS transistors." 16th IEEE Workshop on Low Temperature electronics. No. FZJ-2024-05369. Zentralinstitut für Elektronik, 2024.
- [9] S.Mutum, et. Al, "A Photonic Link at 4.7K with >1 GHz bandwidth towards an Optical Quantum Computing Interface", IEEE MTT-S International Microwave Symposium (IMS) 15-20 June 2025, Moscone Center, San Francisco, CA
- [10] Kammerloher, E. (2022) Improving the output signal of charge readout for quantum computing in electrostatically defined quantum dots with a new sensing dot concept. Dissertation/PhD thesis. Aachen: RWTH Aachen University. DOI: 10.18154/RWTH-2022-01567.

New Spin-Off: icecirc

IceCirc is a spin-off of the Institute for Integrated Computing Architectures at Research Center Jülich which:

- Has 10 years of experience in cryogenic IC design
- Employs state of the art semiconductor technology
- Has demonstrated integration of cryogenic electronics with qubits
- Provides electronic design service for cryogenic integrated electronics

Visit us at [icecirc.com](https://www.icecirc.com)

